TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

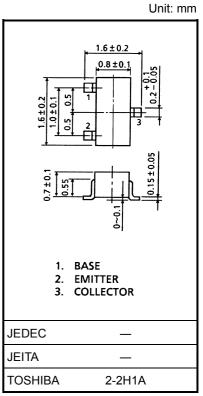
2SC4915

High Frequency Amplifier Applications FM, RF, MIX, If Amplifier Applications

- Small reverse transfer capacitance: $C_{re} = 0.55 \text{ pF (typ.)}$
- Low noise figure: NF = 2.3dB (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	Ic	20	mA
Base current	Ι _Β	4	mA
Collector power dissipation	P _C	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 2.4 mg (typ.)

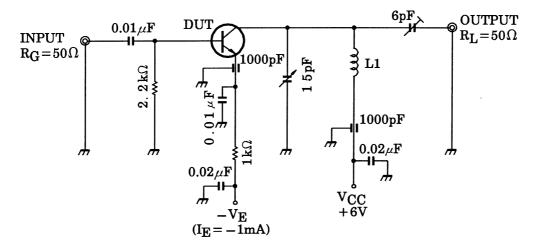
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 40 \text{ V}, I_{E} = 0 \text{ A}$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 4 V, I _C = 0 A	_	_	0.5	μΑ
DC current gain	h _{FE} (Note)	V _{CE} = 6 V, I _C = 1 mA	40	_	200	
Reverse transfer capacitance	C _{re}	V _{CB} = 6 V, f = 1 MHz	_	0.55	_	pF
Transition frequency	f _T	V _{CE} = 6 V, I _C = 1 mA	260	550	_	MHz
Collector-base time constant	C _c ·rbb'	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 30 \text{ MHz}$	_	_	20	ps
Noise figure	NF	V _{CC} = 6 V, I _E = -1 mA, f = 100 MHz, Figure 1	_	2.3	5.0	dB
Power gain	G _{pe}		17	23	_	dB

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Note: h_{FE} classification R: 40~80, O: 70~140, Y: 100~200

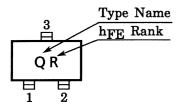
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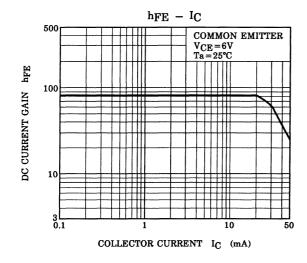
L1: 0.8 mm_{φ} silver plated copper wire, 4 T, 10 mm ID, 8 mm length

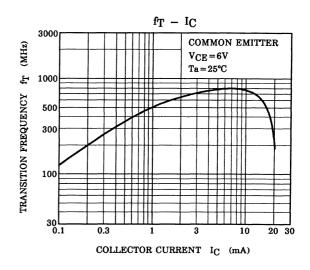
Figure 1 NF, Gpe Test Circuit

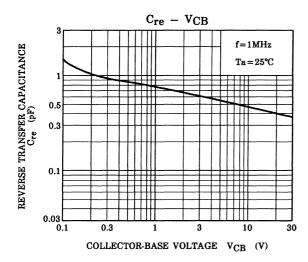
Marking

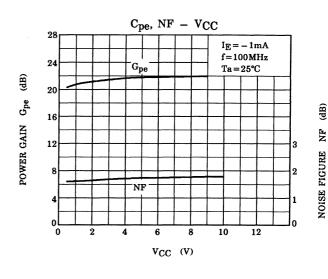


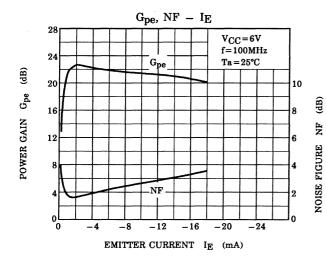
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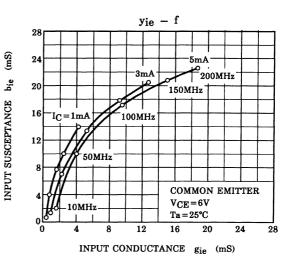








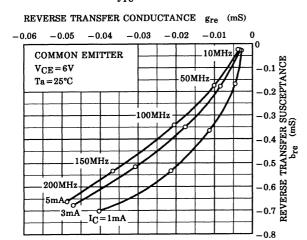




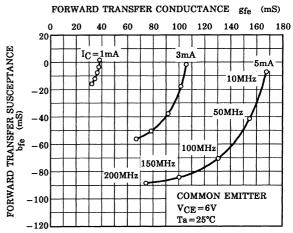
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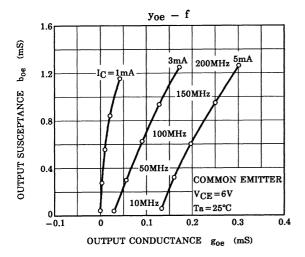
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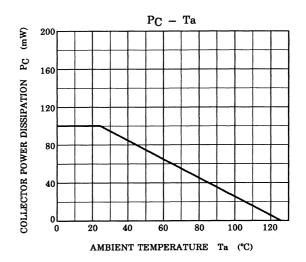
 $y_{re} - f$



 $y_{fe} - f$







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